CA3275

April 1994

Dual Full Bridge Driver

Features

- Two Full Bridge Drivers
- ± 150mA Maximum Current
- Logic Controlled Switching
- Direction Control
- PWM I_{OUT} Control
- 18V Over-Voltage Protection
- 300mA Short-Circuit Protection
- · Nominal 8V to 16V Operation
- Internal Voltage Regulation With Bandgap Reference

Applications

- Dual Full Bridge Driver For Air Core Gauge Instrumentation
- μP Controlled Sensor Data Displays
- Speedometer Displays
- · Tachometer Displays
- · Stepper Motors
- Slave Position Indicators

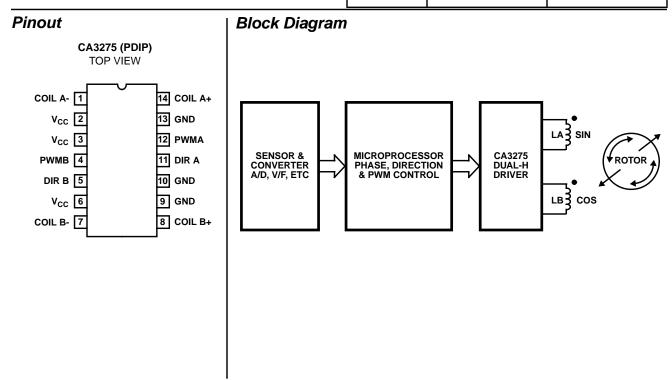
Description

The CA3275 Dual Full Bridge Driver is intended for general-purpose applications requiring Dual Full Bridge drive or switching, including direction and pulse-width modulation for position control. While all features of the IC may not be utilized or required, they would normally be used in instrumentation systems with quadrature coils, such as air-core gauges, where the coils would be driven at frequencies ranging from 200Hz to 400Hz. The coils are wrapped at 90° angles for independent direction control. Coils wound in this physical configuration are controlled by pulse width modulation, where each coil drive is a function of the sine or cosine versus degrees of movement. The direction control is used to change the direction of the current in the H-Driver coil.

The switch rate capability of the IC is typically 30kHz regardless of the inductive load. Over-current limiting is used to limit short circuit current. Over-voltage protection (in the range of 18V to 24V) causes the device to shut down the output current drive. Thermal shutdown limits power dissipation on the chip. The CA3275 is supplied in a 14 lead dual-inline plastic package.

Ordering Information

| PART NO. | TEMPERATURE | PACKAGE |
|----------|----------------|---------------------|
| CA3275E | -40°C to +85°C | 14 Lead Plastic DIP |



Specifications CA3275

Absolute Maximum Ratings

Each Drive

Thermal Information

| Thermal Resistance θ_{JA} |
|--|
| PDIP Package |
| Power Dissipation, P _D |
| Up to +70°C800mW |
| Above +70°C Derate Linearly at 10mW/°C |
| Ambient Temperature Range |
| Operating40°C to +85°C |
| Storage |
| Lead Temperature (During Soldering)+265°C |
| At distance $1/16 + 1/32$ " (1.59 + 0.79mm) from case for 1.0s may |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Specifications $T_A = -40$ °C to +85°C, $V_{CC} = 16$ V Unless Otherwise Specified

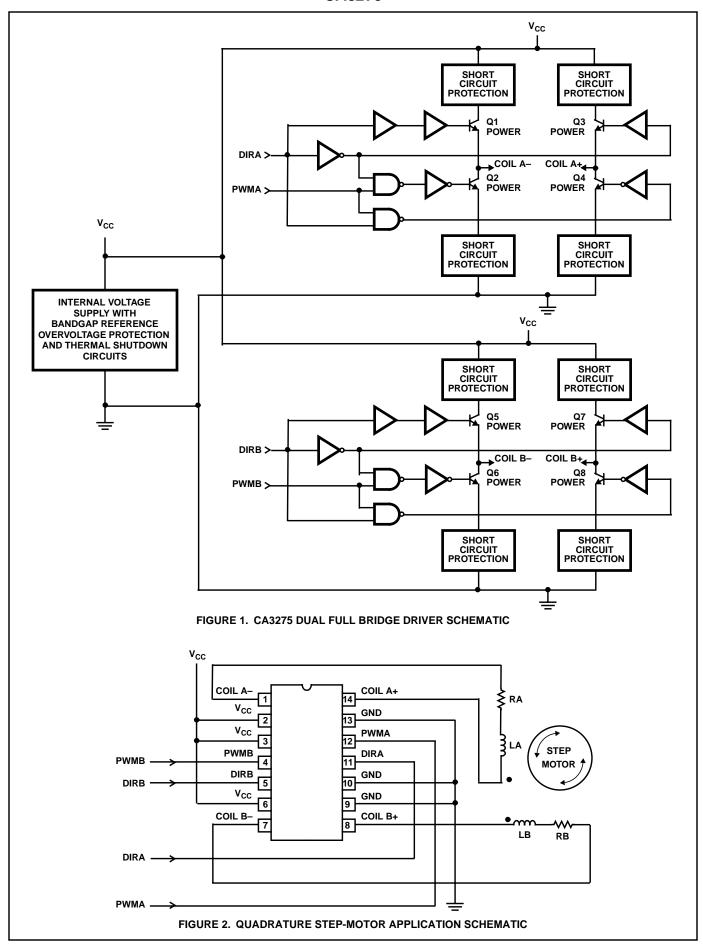
| PARAMETERS | SYMBOL | MIN | TYP | MAX | UNITS |
|---|-------------------------|-----|------|------|-------|
| Operating Supply Voltage Range | V _{CC} | 8 | - | 16 | V |
| Supply Current (Note 1) | I _{CC} | - | 8 | 20 | mA |
| INPUT LEVELS | | | | | |
| Logic Input, Low Voltage | V _{IL} | - | - | 0.8 | V |
| Logic Input, High Voltage | V _{IH} | 3.5 | - | - | V |
| Logic Input, Low Current, V _{IL} = 0V | I _{IL} | -10 | - | - | μΑ |
| Logic Input, High Current, V _{IH} = 5V | Iн | - | - | 10 | μΑ |
| OUTPUT: RLA = RLB = 138Ω | | | | | |
| Maximum Source Saturated Voltage | V _{SAT} - High | - | 1.2 | 1.75 | V |
| Maximum Sink Saturated Voltage | V _{SAT} - Low | - | 0.25 | 0.5 | V |
| Differential V _{SAT} Voltage, Both Outputs Saturated | Diff - V _{SAT} | - | 10 | 100 | mV |

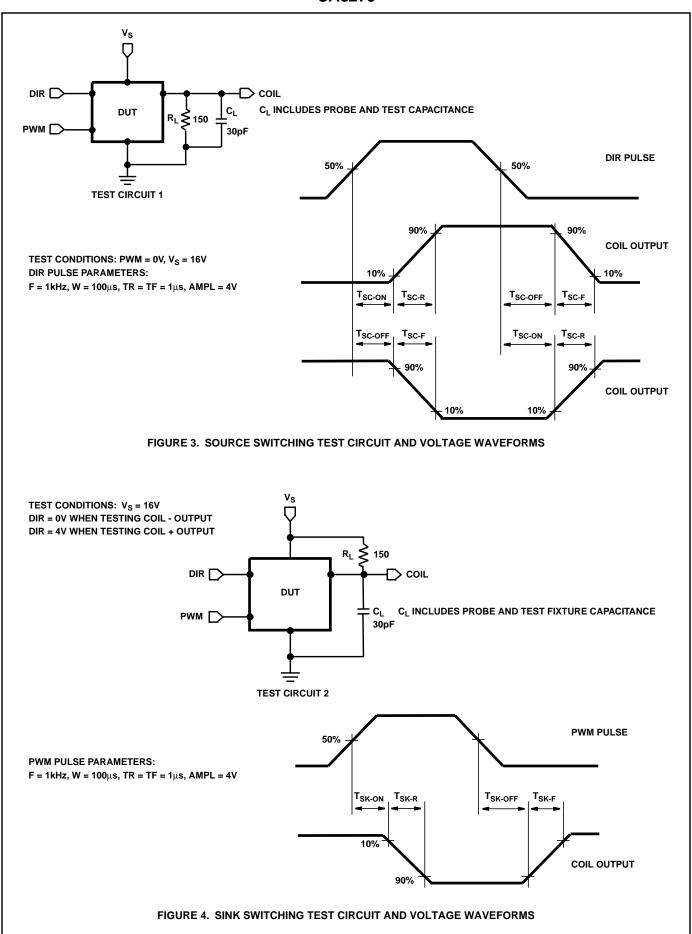
Switching Specifications

| PARAMETERS | SYMBOL | MIN | TYP | MAX | UNITS |
|-------------------------------|---------------------|-----|-----|-----|-------|
| SOURCE CURRENT (See Figure 3) | | • | | | |
| Turn-Off Delay | T _{SC-OFF} | - | - | 2 | μs |
| Fall Time | T _{SC-F} | - | - | 2.2 | μs |
| Turn-On Time | T _{SC-ON} | - | - | 1 | μs |
| Rise Time | T _{SC-R} | - | - | 0.4 | μs |
| SINK CURRENT (See Figure 4) | • | | | | |
| Turn-Off Delay | T _{SK-OFF} | - | - | 1.6 | μs |
| Fall Time | T _{SK-F} | - | - | 0.4 | μs |
| Turn-On Time | T _{SK-ON} | - | - | 0.6 | μs |
| Rise Time | T _{SK-R} | - | - | 0.2 | μs |

NOTE:

1. No load, PWMA = PWMB = 5V, DIR A = DIR B = 0V





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